Dual P-Channel Logical Level MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

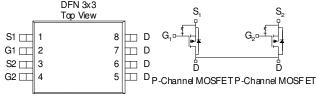
	$V_{DS}(V)$	$\mathbf{r}_{\mathrm{DS(on)}}\left(\mathrm{OHM}\right)$	$I_{D}(A)$
		$0.028 @ V_{GS} = -4.5 V$	6
	-20	$0.045 @ V_{GS} = -2.5V$	4.8
		$0.078 @ V_{GS} = -1.8V$	3.6
$\overline{}$]	DEN 3x3	

PRODUCT SUMMARY

- $\begin{tabular}{ll} \textbf{Low} & r_{DS(on)} & provides & higher efficiency & and \\ extends & battery & life \\ \end{tabular}$
- Low thermal impedance copper leadframe DFN 3x3 saves board space
- Fast switching speed
- High performance trench technology

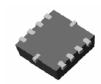


RoHS





ESD Protected 2000V



ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Maximum	Units		
Drain-Source Voltage		V_{DS}	-20	V		
Gate-Source Voltage		V_{GS}	±8	v		
Continuous Drain Current ^a	$T_A=25^{\circ}C$	T_	6			
Continuous Drain Current	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1D	4.9	A		
Pulsed Drain Current ^b			±40			
Continuous Source Current (Diode Conduction) ^a		I_S	1.5	A		
Danie Diagraphic a	$T_A=25^{\circ}C$	\mathbf{D}_{-}	1.5	W		
Power Dissipation ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1 D	1.0			
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Тур	Max				
M . I	t <= 10 sec	D	72	83	0000		
Maximum Junction-to-Ambient ^a	Steady State	R_{thJA}	100	120	°C/W		

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

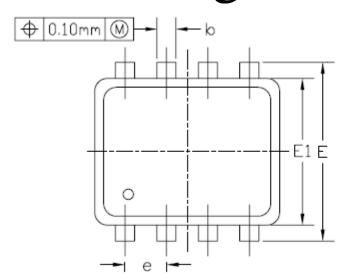
SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	ool Test Conditions		Min Typ		Unit	
Static	•			<u> </u>		•	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}$, $I_D = 250 \text{ uA}$	-0.3			V	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±10	μΑ	
Zero Gate Voltage Drain Current	ī	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ	
Zero Gate Voltage Drain Current	$I_{ m DSS}$	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	μΑ	
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	5			A	
		$V_{GS} = 4.5 \text{ V}, \text{ ID} = 1 \text{ A}$			0.028	Ω	
Drain-Source On-Resistance ^A	$r_{DS(on)}$	$V_{GS} = 2.5 \text{ V}, I_D = 1 \text{ A}$			0.045		
		$V_{GS} = 1.8 \text{ V}, \text{ ID} = 1 \text{ A}$			0.078		
Forward Tranconductance ^A	\mathbf{g}_{fs}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ A}$		25		S	
Diode Forward Voltage ^A	V_{SD}	$I_S = 1 A, V_{GS} = 0 V$		0.8		V	
Dynamic ^b							
Total Gate Charge	Q_{g}			11			
Gate-Source Charge	Q_{gs}	V_{DS} =10V, V_{GS} =4.5V, I_{D} =1A		1.5		пC	
Gate-Drain Charge	Q_{gd}			2.9			
Turn-On Delay Time	$t_{d(on)}$			10			
Rise Time	$t_{\rm r}$	t_r $V_{DD}=10V, V_{GS}=4.5V, I_D=1A$,		70		nS	
Turn-Off Delay Time	$t_{d(off)}$	$R_{\text{GEN}} = 10\Omega$		100		l ns	
Fall-Time	t_{f}			80			

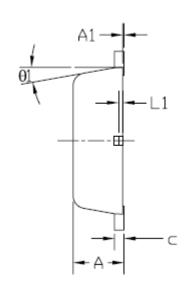
Notes

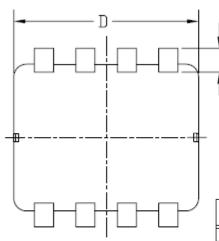
- a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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Package Information







ROT	MOT	VIEW
-	1 0 171	V 1 - 1 1

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.70	0.80	0.90	0.028	0.031	0.035	
A1	0.00		0.05	0.000 — 0.00			
b	0.24	0.30	0.35	0.009	0.012	0.014	
c	0.08	0.15	0.25	0.003	0.006	0.010	
D	2. 90 BSC			0.114 BSC			
E		2.80 BSC		0.110 BSC			
E1	2.30 BSC			0.091 BSC			
e	0.65 BSC			0.026 BSC			
L	0.20	0.38	0.45	0.008	0.015	0.018	
L1	0.05		_	0.002			
θ1	0°	10°	12°	0°	10°	12°	